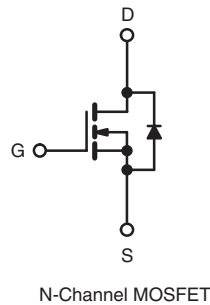
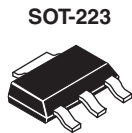


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	100	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.54
Q_g (Max.) (nC)	8.3	
Q_{gs} (nC)	2.3	
Q_{gd} (nC)	3.8	
Configuration	Single	



FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



Available
RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-223 package is designed for surface-mounting using vapor phase, infrared, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of greater than 1.25 W is possible in a typical surface mount application.

ORDERING INFORMATION		
Package	SOT-223	SOT-223
Lead (Pb)-free	IRFL110PbF	IRFL110TRPbF ^a
	SiHFL110-E3	SiHFL110T-E3 ^a
SnPb	IRFL110	IRFL110TR ^a
	SiHFL110	SiHFL110T ^a

Note

- a. See device orientation.

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V_{DS}		100	V
Gate-Source Voltage	V_{GS}		± 20	
Continuous Drain Current	V_{GS} at 10 V	$T_C = 25\text{ }^\circ\text{C}$	1.5	A
		$T_C = 100\text{ }^\circ\text{C}$	0.96	
Pulsed Drain Current ^a	I_{DM}		12	W/ $^\circ\text{C}$
Linear Derating Factor			0.025	
Linear Derating Factor (PCB Mount) ^e			0.017	
Single Pulse Avalanche Energy ^b	E_{AS}		150	mJ
Repetitive Avalanche Current ^a	I_{AR}		1.5	A
Repetitive Avalanche Energy ^a	E_{AR}		0.31	mJ
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$		3.1	W
	$T_A = 25\text{ }^\circ\text{C}$		2.0	
Peak Diode Recovery dV/dt^c	dV/dt		5.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}		- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 25\text{ mH}$, $R_G = 25\text{ }^\circ\Omega$, $I_{AS} = 3.0\text{ A}$ (see fig. 12).
- $I_{SD} \leq 5.6\text{ A}$, $dI/dt \leq 75\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.
- When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	-	60	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	-	40	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$		100	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	0.63	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}$, $V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 0.90\text{ A}^b$	-	-	0.54	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}$, $I_D = 0.90\text{ A}$		1.1	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5		-	180	-	pF
Output Capacitance	C_{oss}			-	81	-	
Reverse Transfer Capacitance	C_{rss}			-	15	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 5.6\text{ A}$, $V_{DS} = 80\text{ V}$, see fig. 6 and 13 ^b	-	-	8.3	nC
Gate-Source Charge	Q_{GS}			-	-	2.3	
Gate-Drain Charge	Q_{GD}			-	-	3.8	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}$, $I_D = 5.6\text{ A}$, $R_G = 24\text{ }\Omega$, $R_D = 8.4\text{ }\Omega$, see fig. 10 ^b		-	6.9	-	ns
Rise Time	t_r			-	16	-	
Turn-Off Delay Time	$t_{d(off)}$			-	15	-	
Fall Time	t_f			-	9.4	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.0	-	nH
Internal Source Inductance	L_S			-	6.0	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	1.5	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	12	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = 1.5\text{ A}$, $V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = 5.6\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	100	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.44	0.88	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

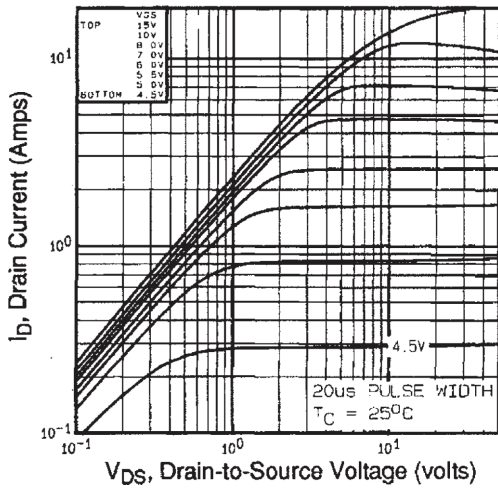


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

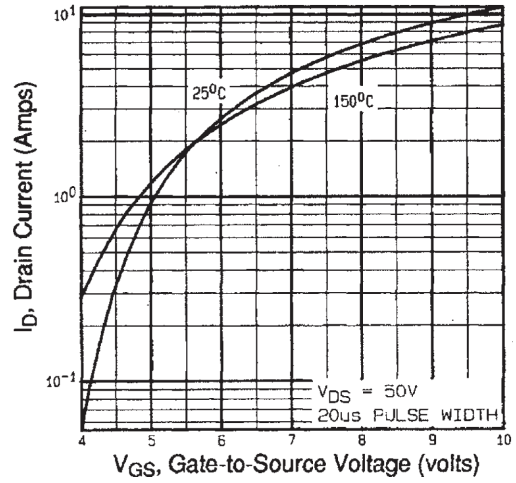


Fig. 3 - Typical Transfer Characteristics

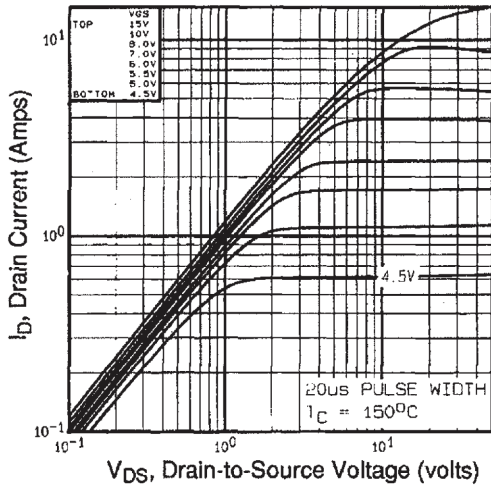


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

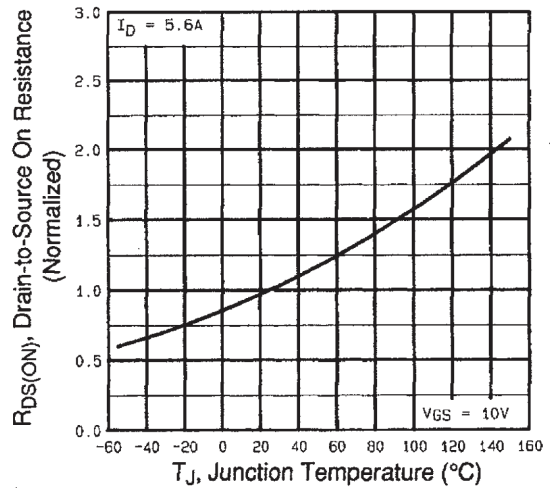


Fig. 4 - Normalized On-Resistance vs. Temperature

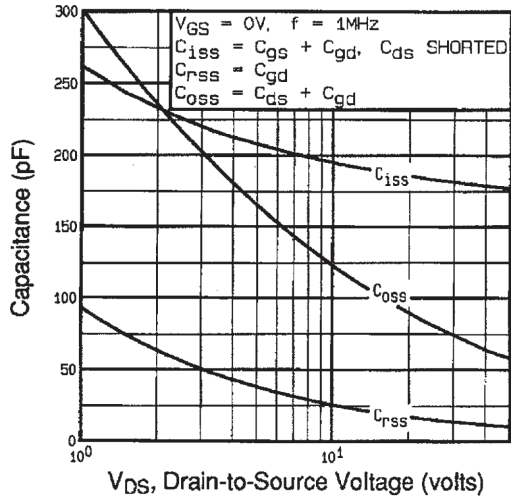


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

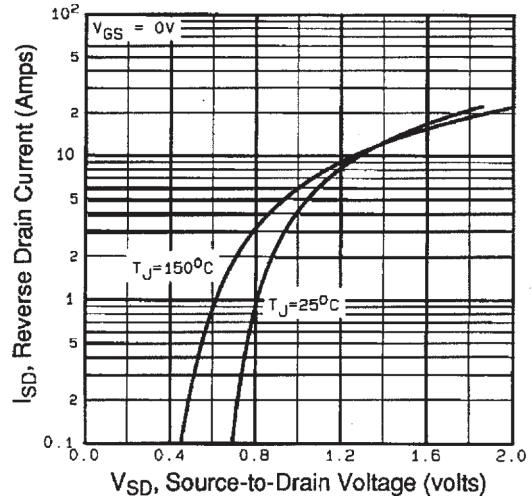


Fig. 7 - Typical Source-Drain Diode Forward Voltage

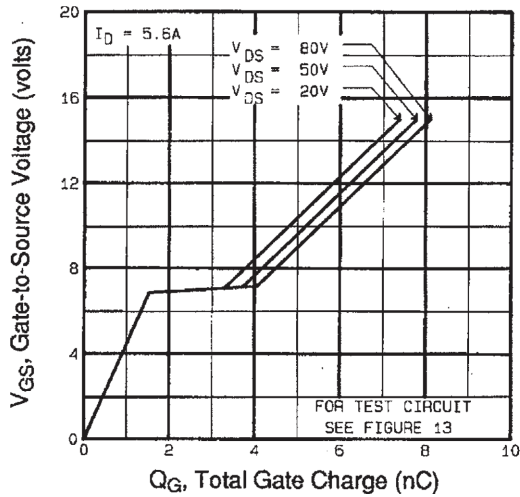


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

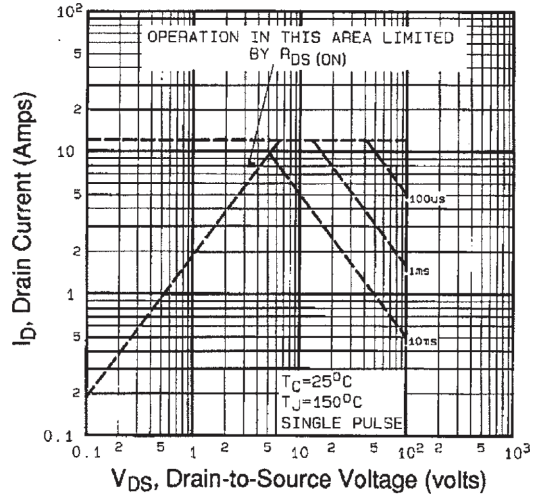


Fig. 8 - Maximum Safe Operating Area

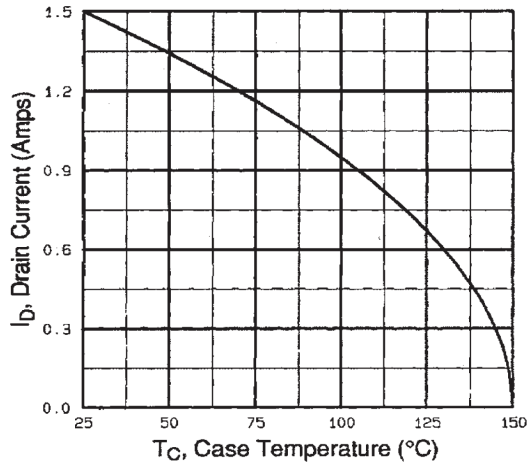


Fig. 9 - Maximum Drain Current vs. Case Temperature

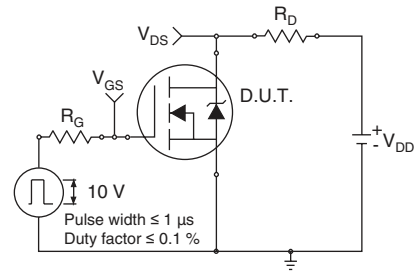


Fig. 10a - Switching Time Test Circuit

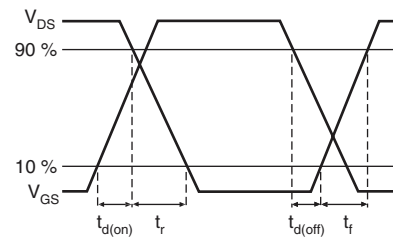


Fig. 10b - Switching Time Waveforms

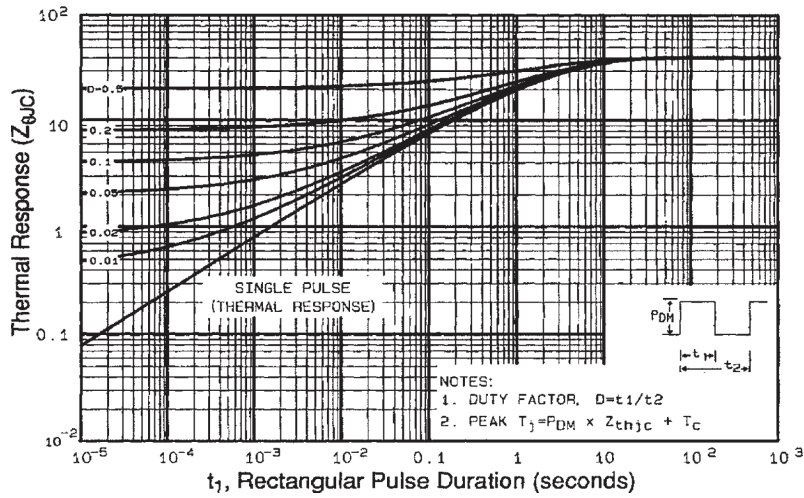


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms

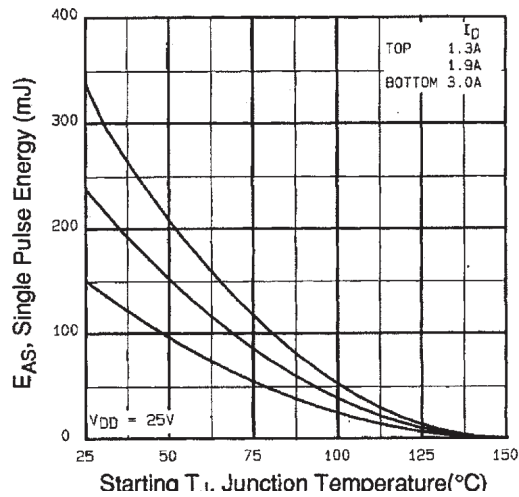


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

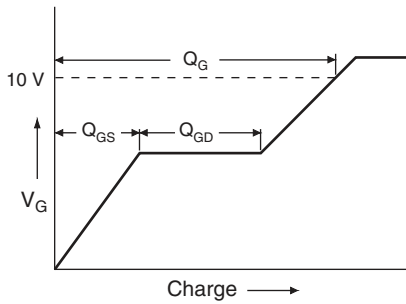


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Fig.14 - For N-Channel

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